

## K3700-VB Datasheet

### N-Channel 900V (D-S) Super Junction Power MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	900	
$R_{DS(on)}$ at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V	0.75
$Q_g$ max. (nC)	20	
$Q_{gs}$ (nC)	2.4	
$Q_{gd}$ (nC)	11	
Configuration	Single	

#### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)

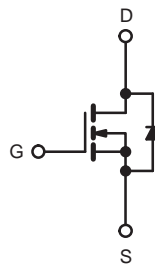
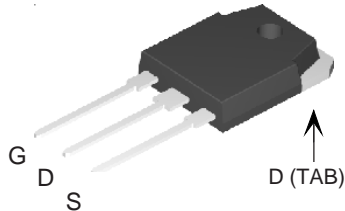


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#### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial

TO-3P



N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	900	V
Gate-Source Voltage			V <sub>GS</sub>	± 30	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	9	A
		T <sub>C</sub> = 100 °C		7.3	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	28	
Linear Derating Factor				1.89	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	86	mJ
Maximum Power Dissipation			P <sub>D</sub>	109	W
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Drain-Source Voltage Slope	T <sub>J</sub> = 125 °C		dV/dt	50	V/ns
Reverse Diode dV/dt <sup>d</sup>		3.2			
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s			300	°C


#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 3.5$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	72	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.7	

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		900	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.65	-	V/°C
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2	-	4	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
		V <sub>GS</sub> = ± 30 V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 900 V, V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> =620 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	10	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A	-	0.75	-	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 6 A		-	19	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz		-	373	-	pF
Output Capacitance	C <sub>oss</sub>			-	26	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	14	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	C <sub>O(er)</sub>	V <sub>DS</sub> = 0 V to 520 V, V <sub>GS</sub> = 0 V		-	46	-	pF
Effective Output Capacitance, Time Related <sup>b</sup>	C <sub>O(tr)</sub>			-	64	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, V <sub>DS</sub> = 520 V	-	26	-	nC
Gate-Source Charge	Q <sub>gs</sub>			-	2.1	-	
Gate-Drain Charge	Q <sub>gd</sub>			-	2.8	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 620 V, I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω		-	26	-	ns
Rise Time	t <sub>r</sub>			-	55.7	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	71	-	
Fall Time	t <sub>f</sub>			-	41	-	
Gate Input Resistance	R <sub>g</sub>	f = 1 MHz, open drain		-	3.5	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7	A
Pulsed Diode Forward Current	I <sub>SM</sub>			-	-	18	
Diode Forward Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 6 A, V <sub>GS</sub> = 0 V		-	-	1.4	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 6 A, dI/dt = 100 A/μs, V <sub>R</sub> = 400 V		-	192	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>			-	2.4	-	μC
Reverse Recovery Current	I <sub>RRM</sub>			-	11	-	A

**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

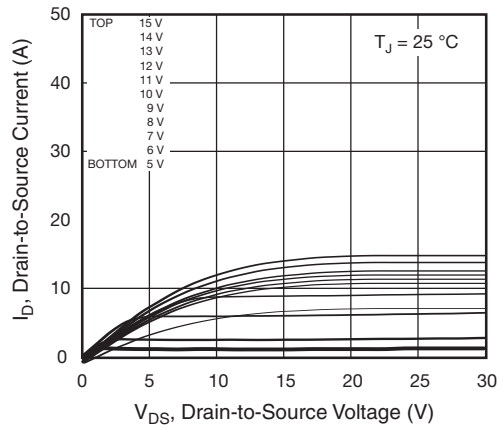
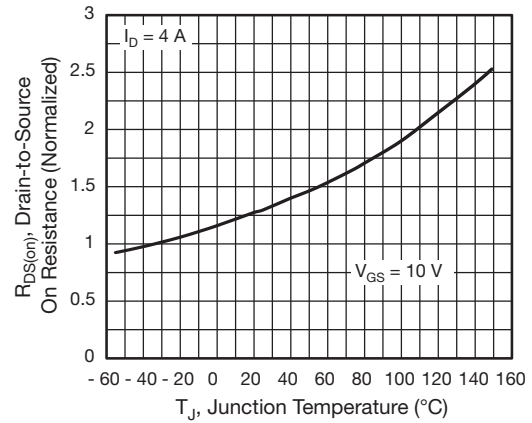
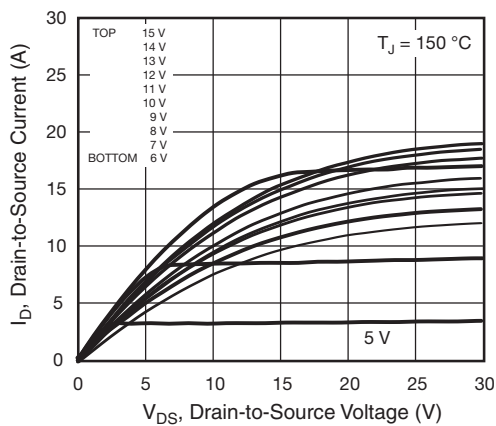
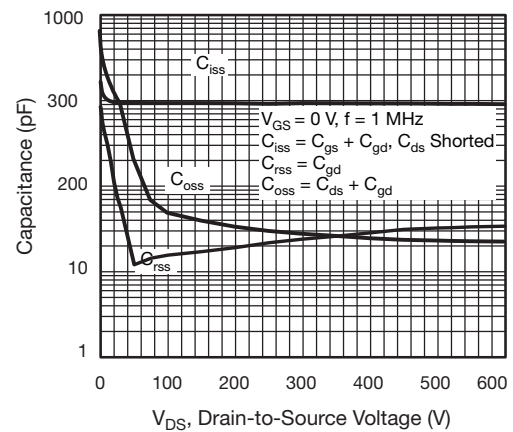
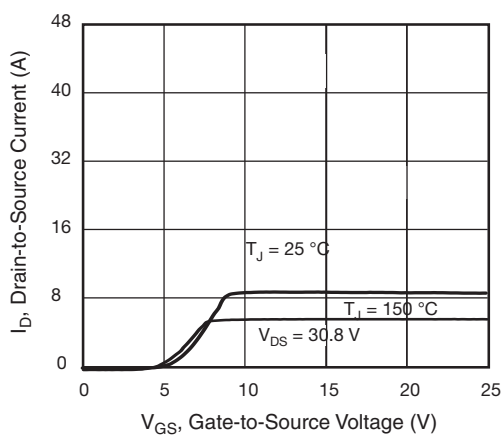
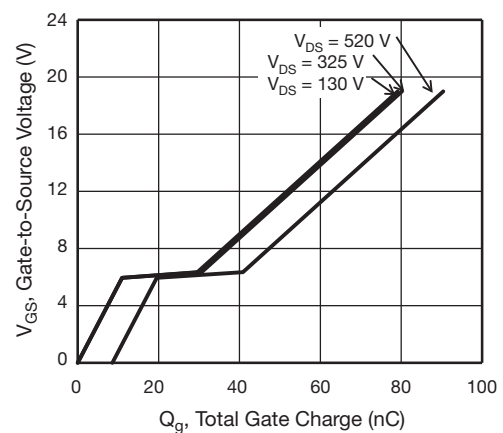
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 8 - Maximum Safe Operating Area



Fig. 10 - Temperature vs. Drain-to-Source Voltage

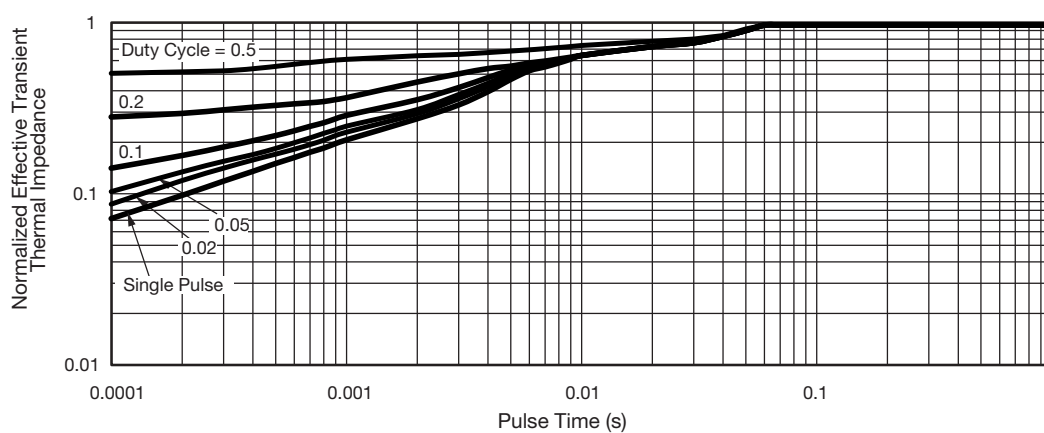


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

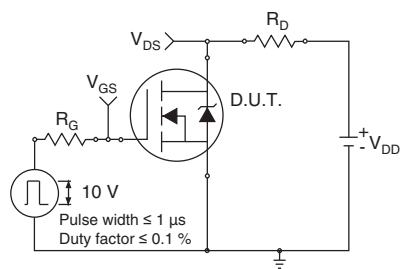


Fig. 12 - Switching Time Test Circuit



Fig. 16 - Basic Gate Charge Waveform

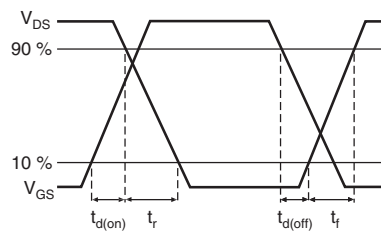


Fig. 13 - Switching Time Waveforms

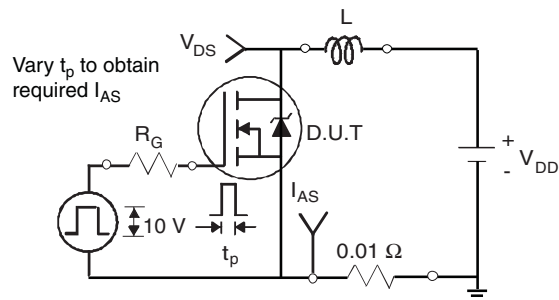


Fig. 14 - Unclamped Inductive Test Circuit

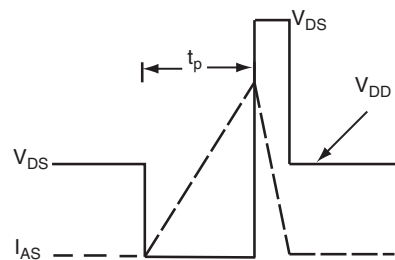


Fig. 15 - Unclamped Inductive Waveforms

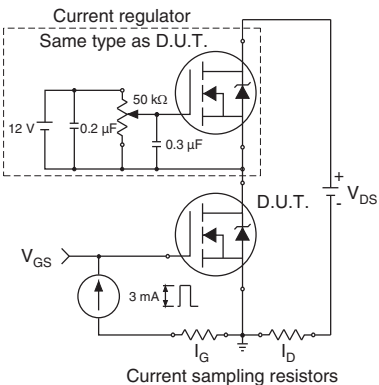


Fig. 17 - Gate Charge Test Circuit

### Peak Diode Recovery $dV/dt$ Test Circuit



**Fig. 18 - For N-Channel**

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